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CUSTOMER	NO. SST 6427
	PAGE 1 of 2
SUBJECT TRANSISTOR, NPN ,SILICON	DATE

ELECTRICAL CHARACTERISTICS: (Ta = 25°C Unless Otherwise Specified)

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
$BV_{CBO}$	$I_C = 100 \mu A$	40			V
$BV_{CEO}$	$I_C = 10 \text{ mA}$	40			V
$BV_{EBO}$	$I_E = 10 \mu A$	12			V
$I_{CBO}$	$V_{CB} = 30 \text{ V}$			50	nA
$I_{CEO}$	$V_{CE} = 25 \text{ V}$			1.0	$\mu A$
$I_{EBO}$	$V_{BE} = 10 \text{ V}$			50	nA
$H_{FE}$	$I_C = 10 \text{ mA}, V_{CE} = 5.0 \text{ V}$	10,000		100,000	
$H_{FE}$	$I_C = 100 \text{ mA}, V_{CE} = 5.0 \text{ V}$	20,000		200,000	
$H_{FE}$	$I_C = 500 \text{ mA}, V_{CE} = 5.0 \text{ V}$	14,000		140,000	
$V_{CE(SAT)}$	$I_C = 50 \text{ mA}, I_B = 0.5 \text{ mA}$		0.71	1.2	V
$V_{CE(SAT)}$	$I_C = 500 \text{ mA}, I_B = 0.5 \text{ mA}$		0.9	1.5	V
$V_{BE(SAT)}$	$I_C = 500 \text{ mA}, I_B = 0.5 \text{ mA}$		1.52	2.0	V
$V_{BE(ON)}$	$I_C = 50 \text{ mA}, V_{CE} = 5.0 \text{ V}$		1.24	1.75	V
$C_{ob}$	$V_{CB} = 10 \text{ V}, I_E = 0, f = 1.0 \text{ MHz}$		5.4	7.0	pF
$C_{ib}$	$V_{BE} = 1.0 \text{ V}, I_C = 0, f = 1.0 \text{ MHz}$		10	15	pF
$h_{ie}$	$I_C = 10 \text{ mA}, V_{CE} = 5 \text{ V}, f = 1.0 \text{ KHz}$	50		1000	$K\Omega$
$h_{fe}$	$I_C = 10 \text{ mA}, V_{CE} = 5 \text{ V}, f = 1.0 \text{ KHz}$	10,000			
$h_{oe}$	$I_C = 10 \text{ mA}, V_{CE} = 5 \text{ V}, f = 1.0 \text{ KHz}$			1000	umhos
NF	$I_C = 1.0 \text{ mA}, V_{CE} = 5 \text{ V}, R_S = 100K\Omega$ $f = 10 \text{ KHz to } 15.7 \text{ KHz}$		3.0	10	dB

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APPROVAL

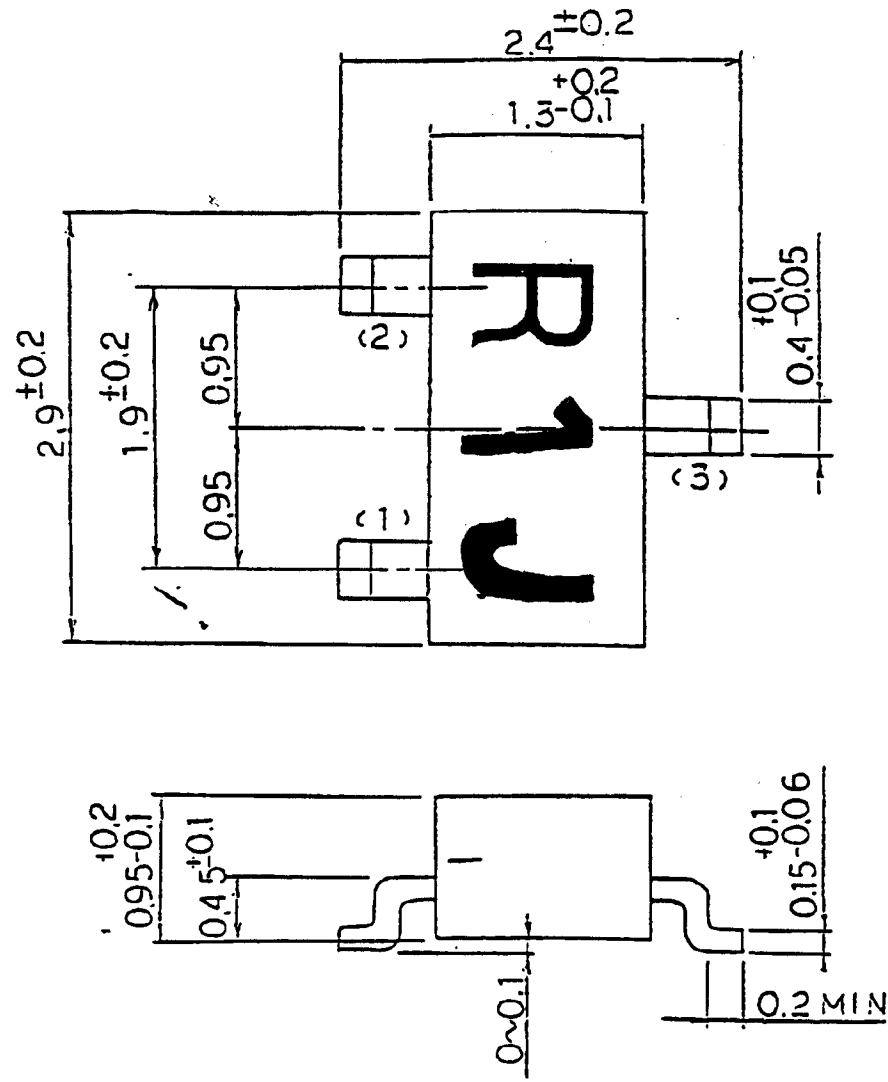
*T. Shirota*  
80-18-99

CHECK

*FDW*  
5/24/99

DESIGN

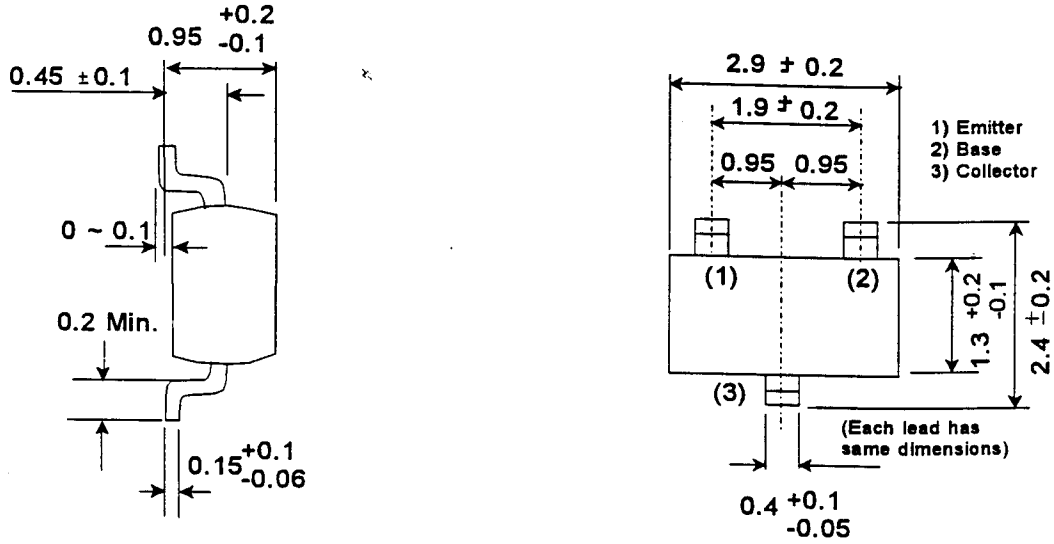
**MASTER**



UNIT: mm

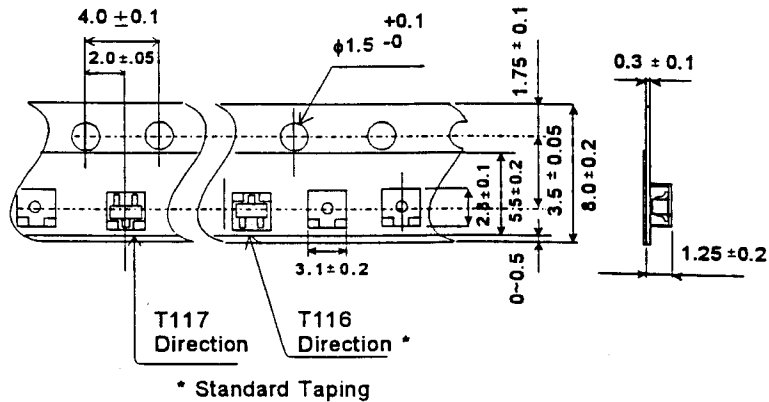
- (1) Emitter
- (2) Base
- (3) Collector

SST (EUROPEAN SOT23) PACKAGE



Unit: mm

- 1) Emitter
- 2) Base
- 3) Collector



MASTER